

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:	)	PATENT APPLICATION
	)	
Inventors: Douglas J. Tweet, Jong-Jan Lee	)	
And Jer-Shen Maa	)	
	)	
Serial No.: Not Yet Assigned	)	Attorney Docket No.
	)	SLA 0735
Filed: Herewith	)	
	)	
Title: LOW TEMPERATURE ANNEAL	)	
TO REDUCE DEFECTS IN	)	
HYDROGEN-IMPLANTED	)	
RELAXED SiGe LAYER	)	

Honorable Commissioner for Patents  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97**

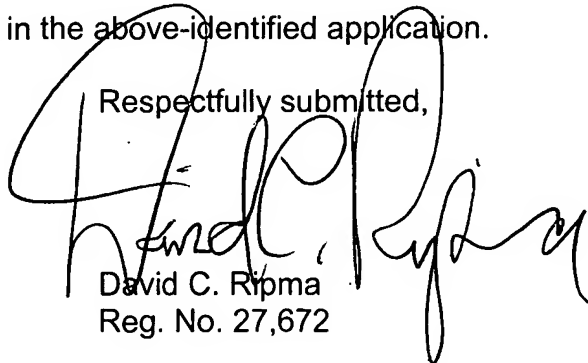
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to  
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by  
the Examiner and made of record in the above-identified application.

(Date) 2/17/04

Respectfully submitted,

  
David C. Ripma  
Reg. No. 27,672

David C. Ripma, Patent Counsel  
Sharp Laboratories of America, Inc.  
5750 NW Pacific Rim Boulevard, Camas, WA 98607  
Telephone: (360) 834-8754  
Facsimile: (360) 817-8505



<b>1449A/PTO</b> Rev. 10/95		<b>U.S. Department of Commerce</b> Patent and Trademark Office		<b>Complete If Known</b>	
				Application Number	
				Filing Date	February 17, 2004
				First Named Inventor	DOUGLAS JAMES TWEET
				Group Art Unit	
				Examiner Name	
<b>LIST OF PRIOR ART CITED BY APPLICANT</b>  (use as many sheets as necessary)				Sheet 1 of 2	Attorney Docket No. SLA.0735

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document Kind Number Code <sup>2</sup> (if known)		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear
		6,464,780	B1	Mantl et al.	10-15-02	
		6,562,703	B1	Maa et al.	05-13-03	
		2003/0143783	A1	Maa et al.	07-31-03	

FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	T <sup>6</sup>
		Office <sup>3</sup> Code <sup>5</sup>	Number <sup>4</sup>	Kind				

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T <sup>2</sup>

Examiner Signature		Date Considered	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1<sup>6</sup> if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached



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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
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		RIM <i>et al.</i> , <i>Strained Silicon NMOSFETs for high performance CMOS technology</i> , 2001 Symposium on VLSI Technology Digest of Technical Papers, p. 59, IEEE (2001)	
		NAYAK <i>et al.</i> , <i>High-mobility Strained-Silicon PMOSFETs</i> , IEEE Transactions on Electron Devices, Vol. 43, 1709 (1996)	
		WELDON <i>et al.</i> , <i>On the mechanism of the hydrogen-induced exfoliation of silicon</i> , J. Vac. Sci. Technol. B. 15, 1065, (1997)	
		MANTL <i>et al.</i> , <i>Strain relaxation of epitaxial SiGe layers on Silicon(100) improved by hydrogen implantation</i> , Nuclear Instruments and Methods in Physics Research B 147, 29, (1999)	
		TRINKAUS <i>et al.</i> , <i>Strain relaxation mechanism for hydrogen-implanted Si<sub>1-x</sub>Ge<sub>x</sub>/Silicon(100) heterostructures</i> , Appl. Phys. Lett., 76, 3552, (2000)	
		CEROFOLINI, <i>et al.</i> , <i>Hydrogen-related complexes as the stressing species in high-fluence, hydrogen-implanted, single-crystal silicon</i> , Physical Review B, vol. 46, p. 2061 (1992)	
		FRABBONI <i>et al.</i> , <i>Static disorder depth profile in ion implanted materials by means of large angle convergent beam electron diffraction</i> , Physical Review Letters, vol. 81, 3155 (1998)	
		FRABBONI, <i>Lattice strain and static disorder in hydrogen-implanted and annealed single-crystal silicon as determined by large-angle convergent-beam electron diffraction</i> , Physical Review B, vol. 65, 165436 (2002)	

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